

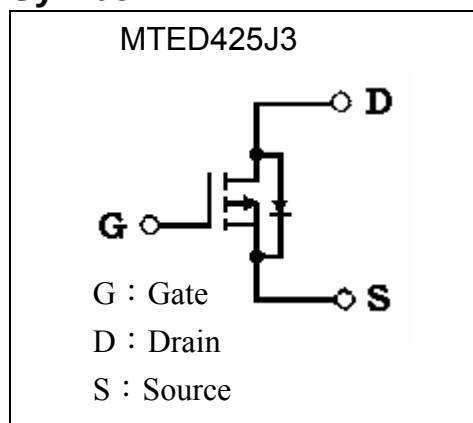
P-Channel Enhancement Mode Power MOSFET

BV_{DSS}	-30V
I_D	-55A
R_{DS(ON)}@V_{GS}=-10V, I_D=-12A	9.7mΩ (typ)
R_{DS(ON)}@V_{GS}=-5V, I_D=-9A	14mΩ (typ)

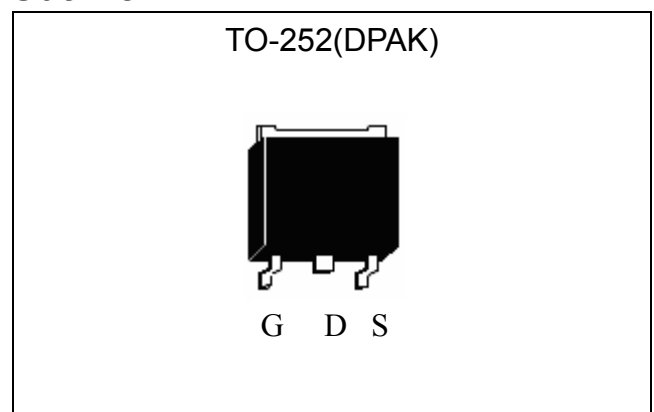
Features

- Single Drive Requirement
- Low On-resistance
- Fast switching Characteristic
- Pb-free lead plating and halogen-free package

Symbol

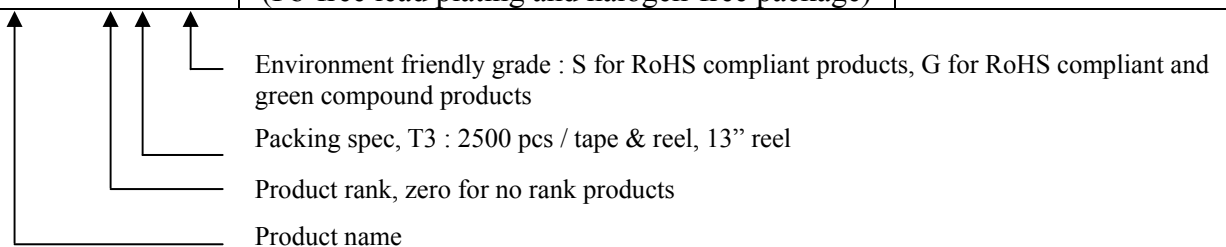


Outline



Ordering Information

Device	Package	Shipping
MTED425J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	
Continuous Drain Current @V _{GS} =-10V, T _C =25°C		I _D	-55	A
Continuous Drain Current @V _{GS} =-10V, T _C =100°C			-35	
Continuous Drain Current @V _{GS} =-10V, T _A =25°C			-12	
Continuous Drain Current @V _{GS} =-10V, T _A =100°C			-7.6	
Pulsed Drain Current		I _{DM}	-150 *1	
Power Dissipation	T _C =25°C	P _D	62 *4	W
	T _C =100°C		25 *4	
	T _A =25°C		2.5	
	T _A =100°C		1.0	
Single Pulse Avalanche Energy		E _{AS}	72 *2	mJ
Single Pulse Avalanche Current		I _{AS}	-38	A
Operating Junction and Storage Temperature		T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	2.5	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{th,j-a}	50 *3	°C/W

Note : *1. Pulse width limited by safe operating area.

*2 . T_j=25°C, V_{DD}=-15V, L=0.5mH, R_G=25Ω.

*3 . The value of R_{th,j-a} is measured with the device mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

*4 . The power dissipation P_D is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determined the current rating, when this rating falls below the package limit.

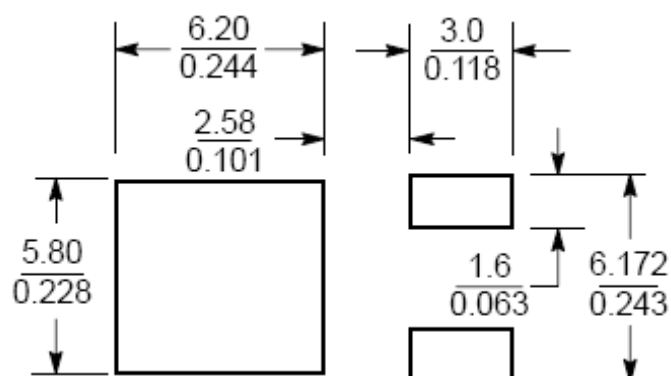
Characteristics (T_j=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0, I _D =-250μA
V _{GS(th)}	-1.0	-1.7	-3	V	V _{DS} = V _{GS} , I _D =-250μA
G _{FS}	-	31	-	S	V _{DS} =-5V, I _D =-12A
I _{GSS}	-	-	±100	nA	V _{GS} =±25
I _{DSS}	-	-	-1	μA	V _{DS} =-24V, V _{GS} =0
I _{DSS}	-	-	-10		V _{DS} =-20V, V _{GS} =0, T _j =125°C
*R _{DS(ON)}	-	9.7	12	mΩ	V _{GS} =-10V, I _D =-12A
*R _{DS(ON)}	-	14	18		V _{GS} =-5V, I _D =-9A
Dynamic					
*Q _g	-	55	-	nC	I _D =-12A, V _{DS} =-15V, V _{GS} =-10V
*Q _{gs}	-	8.7	-		
*Q _{gd}	-	13	-		

*t _{d(ON)}	-	15	-	ns	V _{DS} =-15V, V _{GS} =-10V, R _G =6Ω, I _D =-12A
*t _r	-	18	-		
*t _{d(OFF)}	-	38	-		
*t _f	-	22	-		
C _{iss}	-	2740	-	pF	V _{GS} =0V, V _{DS} =-15V, f=1MHz
C _{oss}	-	376	-		
C _{rss}	-	321	-		
Source-Drain Diode					
*V _{SD}	-	-0.75	-1.2	V	I _S =-3A, V _{GS} =0V
*I _S	-	-	-51	A	
*t _{rr}	-	20	-	ns	I _S =-12A, V _{GS} =0, dI/dt=100A/μs
*Q _{rr}	-	12	-	nC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

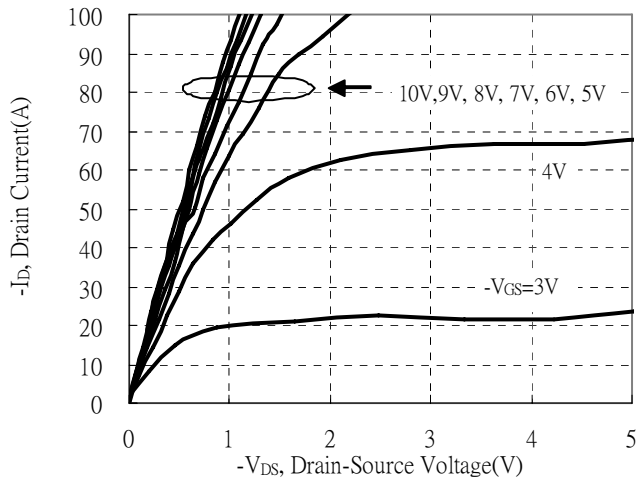
Recommended soldering footprint



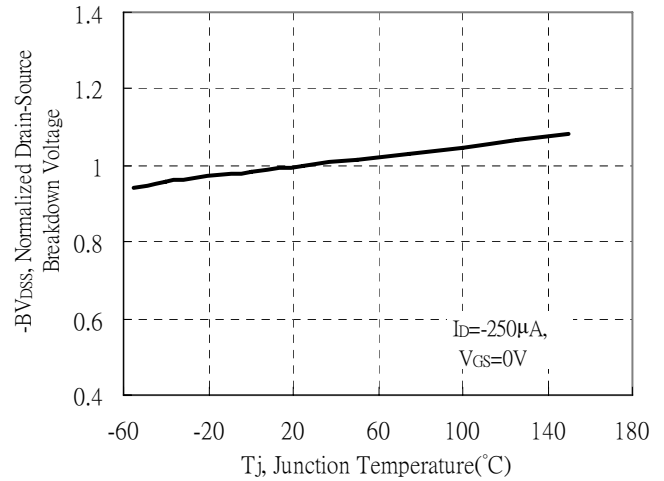
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

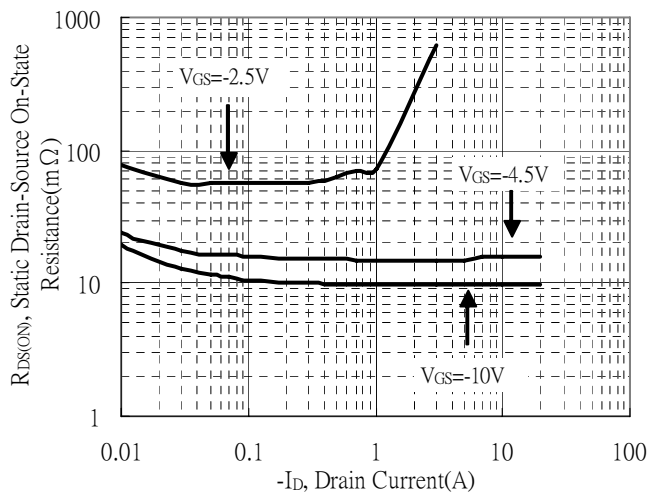
Typical Output Characteristics



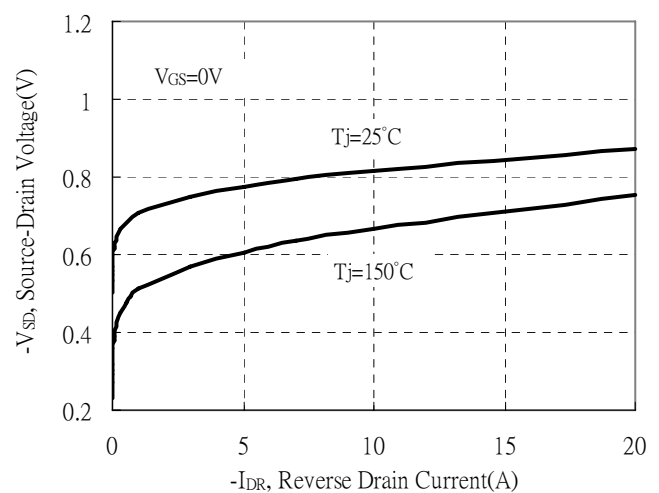
Breakdown Voltage vs Ambient Temperature



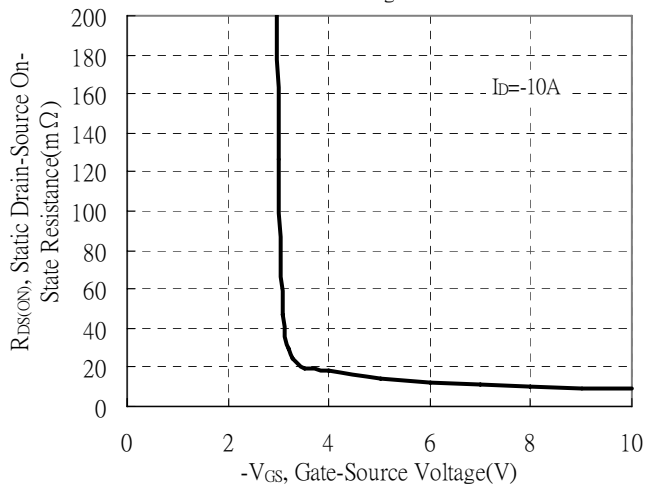
Static Drain-Source On-State resistance vs Drain Current



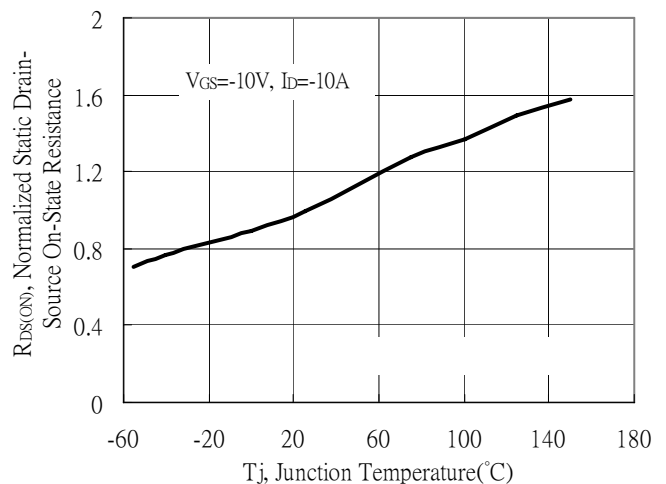
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

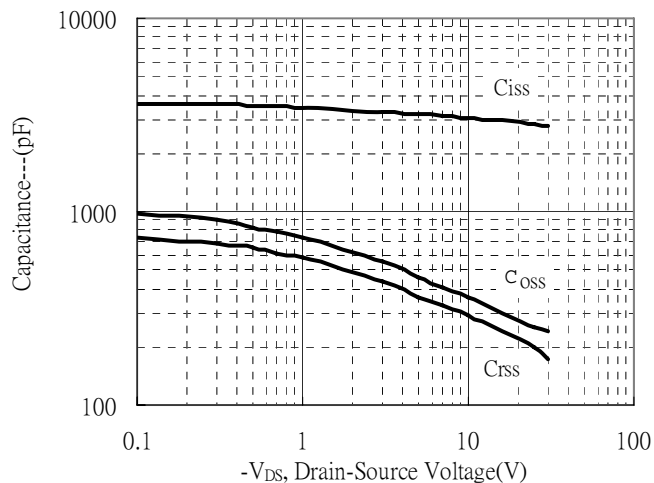


Drain-Source On-State Resistance vs Junction Temperature

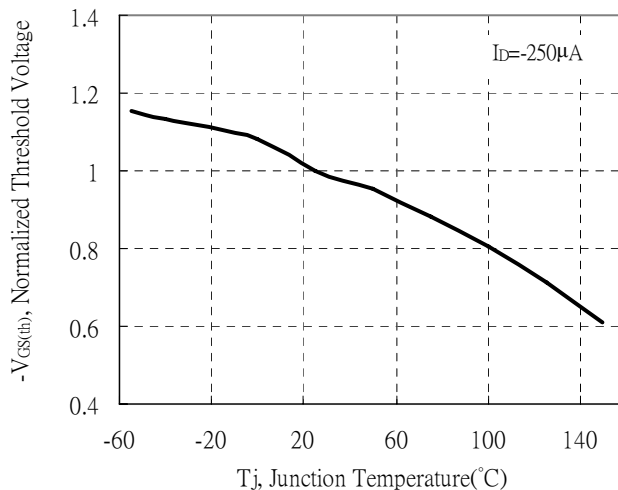


Typical Characteristics(Cont.)

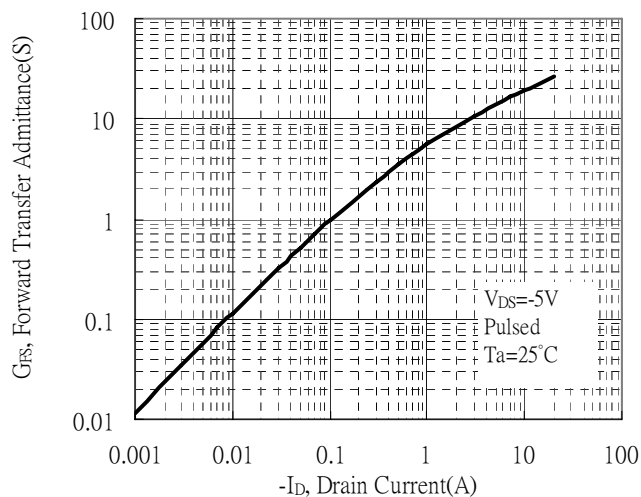
Capacitance vs Drain-to-Source Voltage



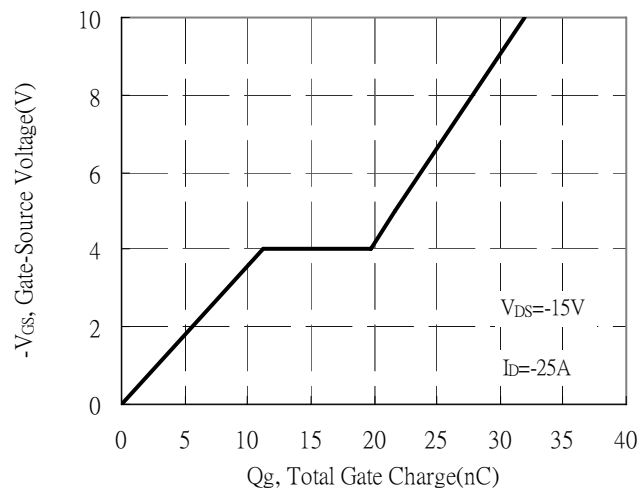
Threshold Voltage vs Junction Temperature



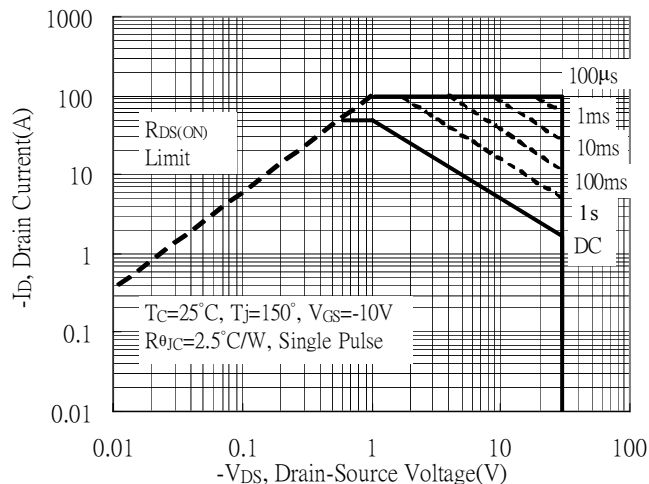
Forward Transfer Admittance vs Drain Current



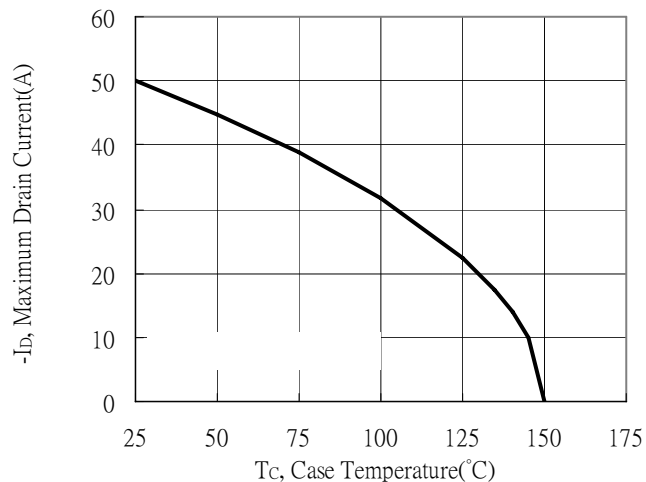
Gate Charge Characteristics



Maximum Safe Operating Area

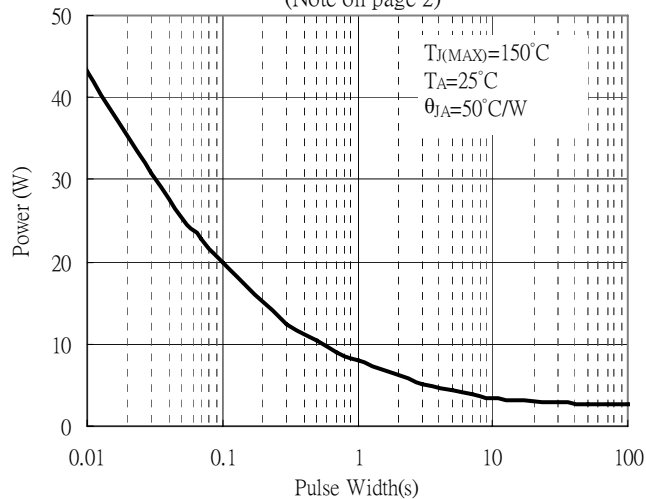


Maximum Drain Current vs Case Temperature

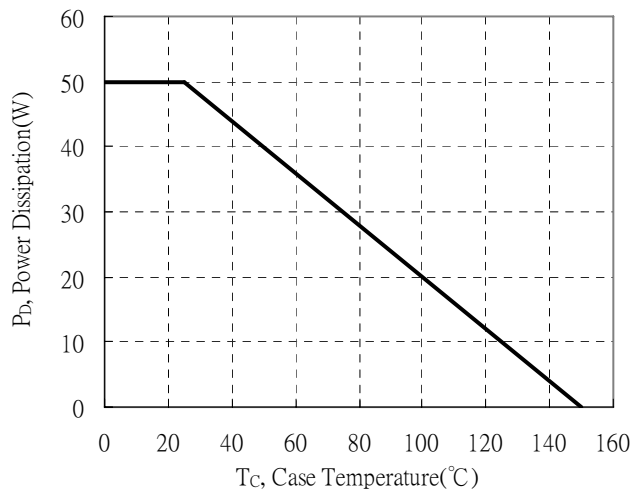


Typical Characteristics(Cont.)

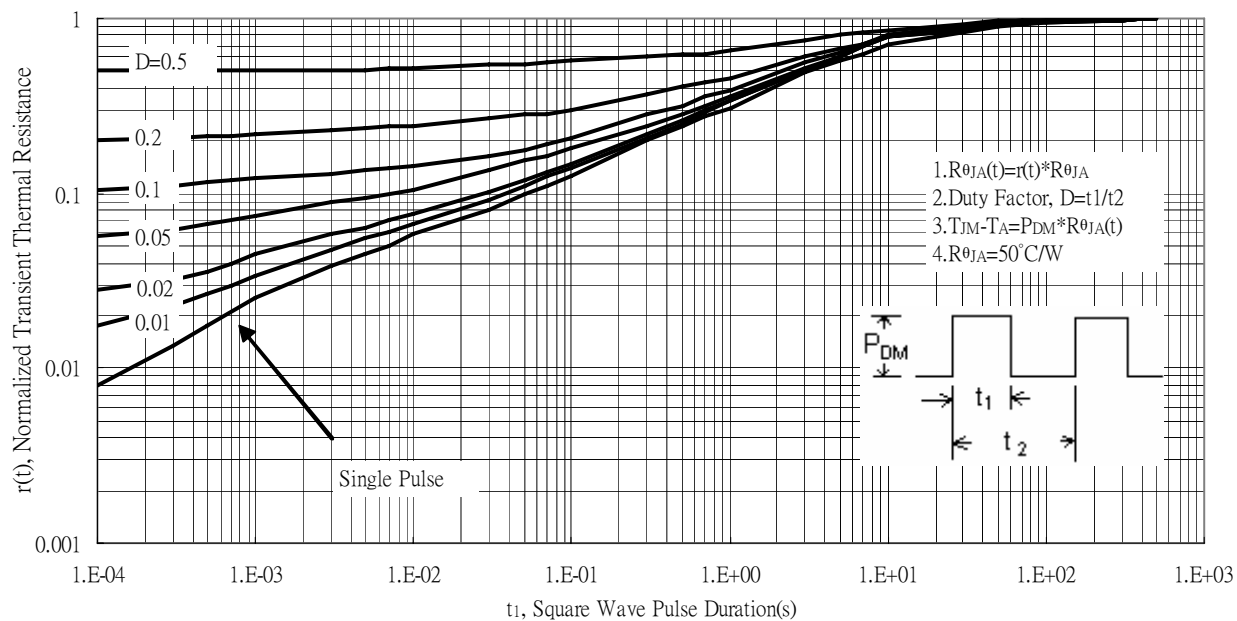
Single Pulse Power Rating, Junction to Ambient
(Note on page 2)



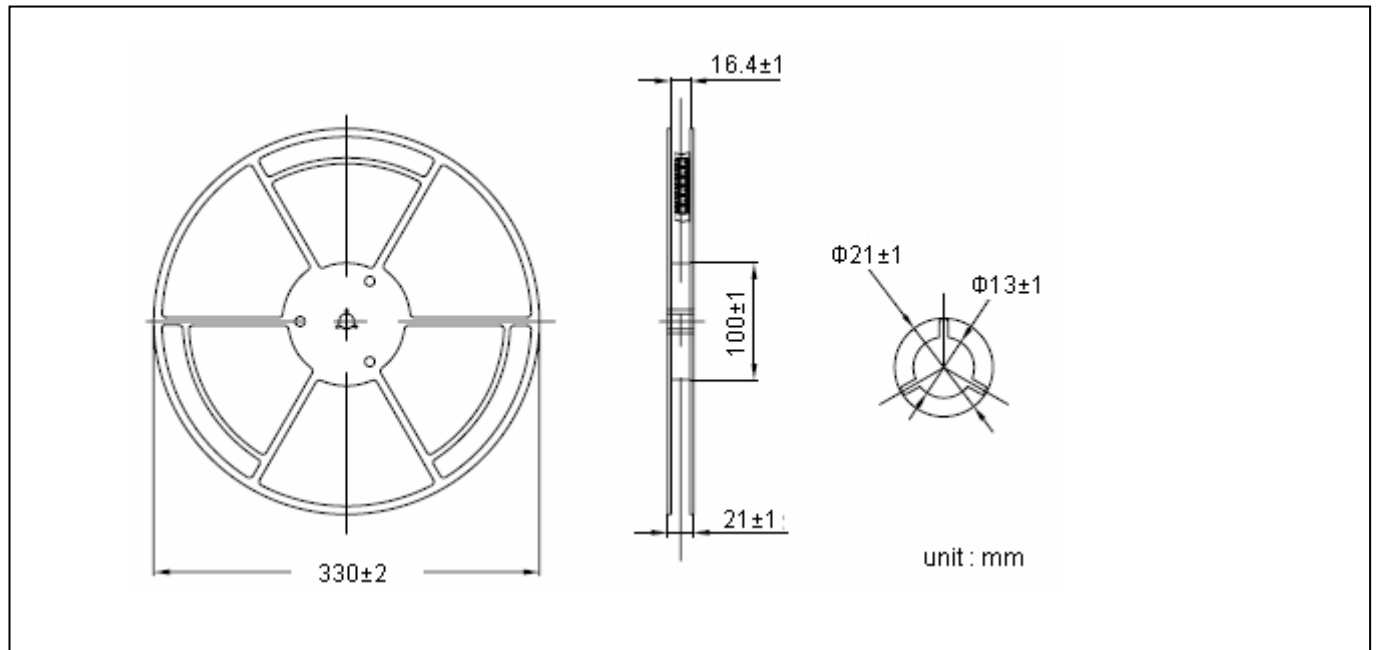
Power Derating Curve



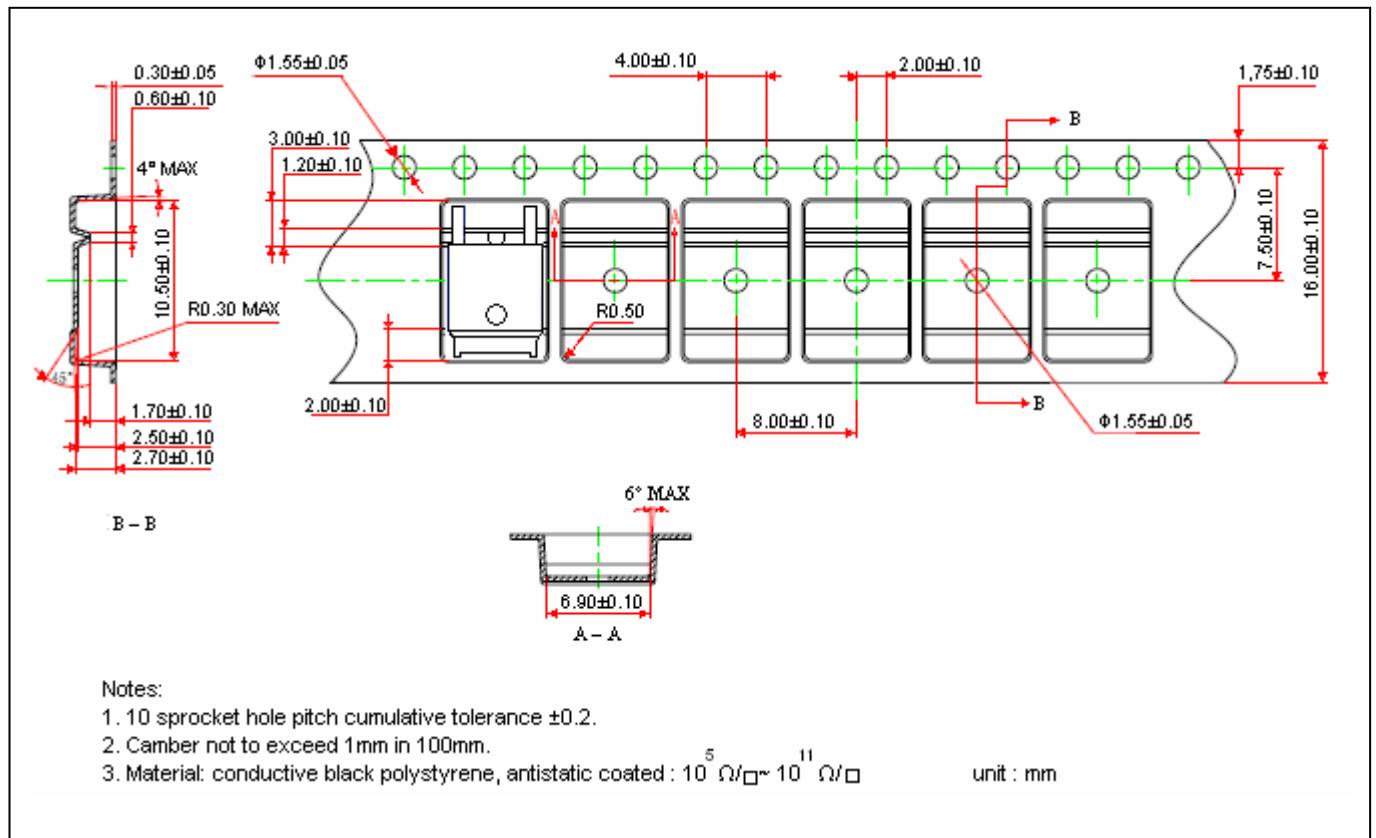
Transient Thermal Response Curves



Reel Dimension



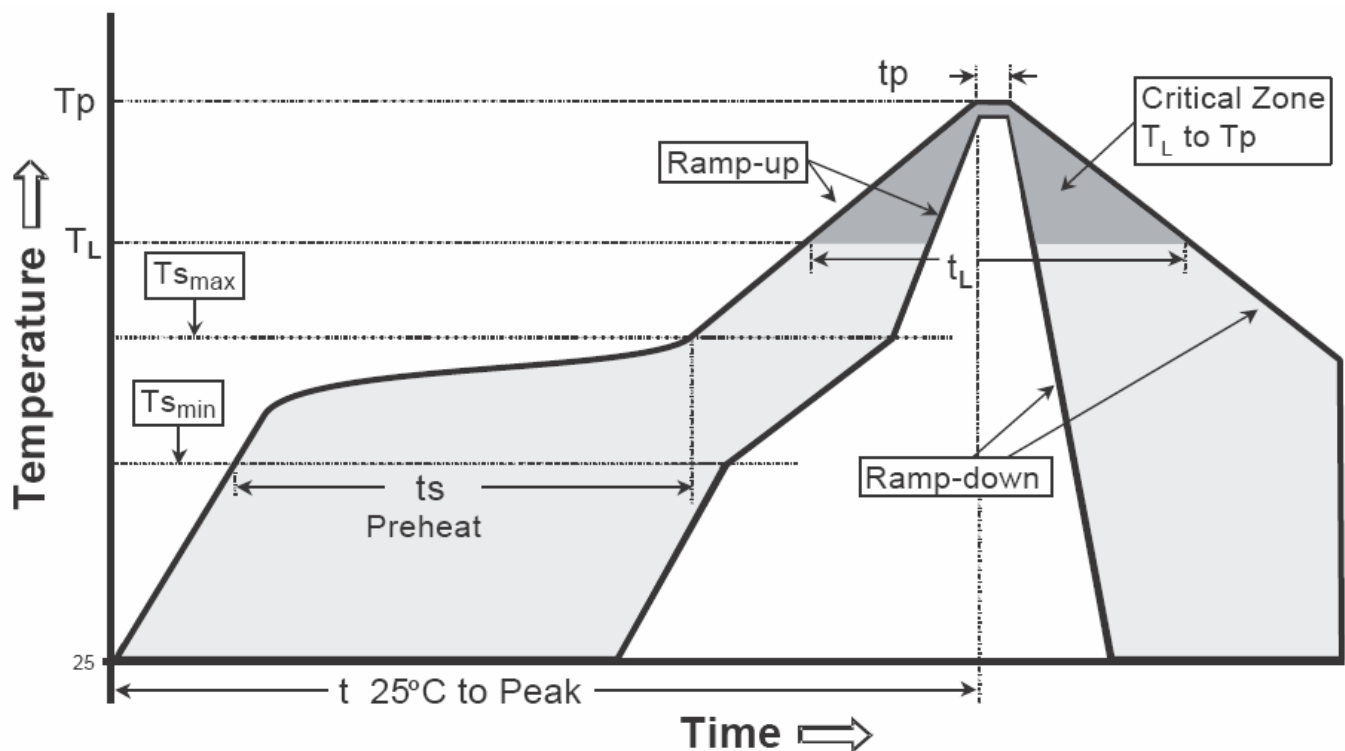
Carrier Tape Dimension



Recommended wave soldering condition

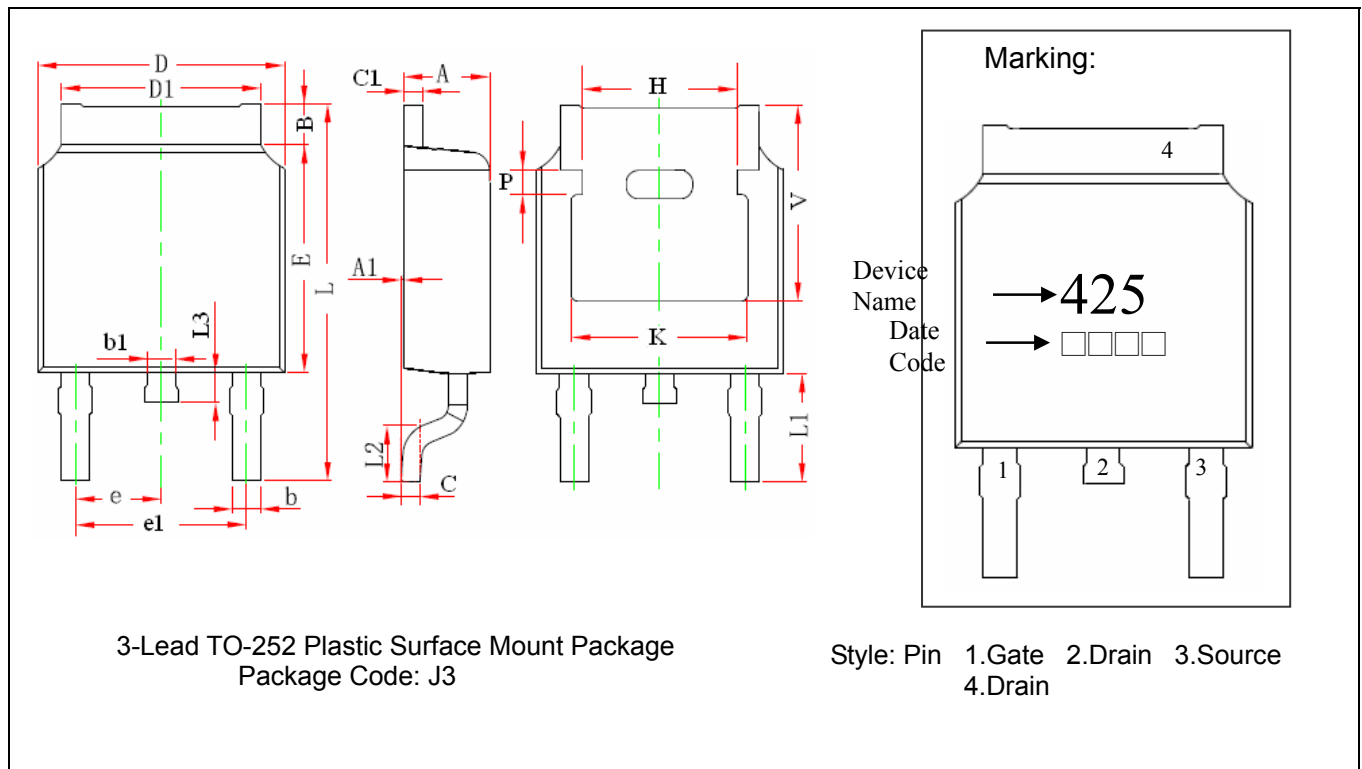
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T_{smax} to T_p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T_{smin})	100°C	150°C
-Temperature Max(T_{smax})	150°C	200°C
-Time(t_{smin} to t_{smax})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T_L)	183°C	217°C
- Time (t_L)	60-150 seconds	60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t_p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-252 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.